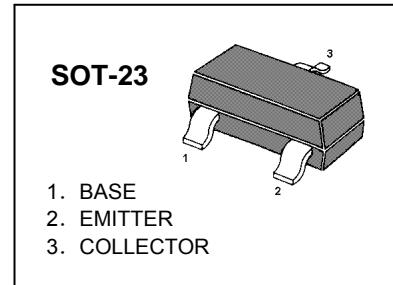


BCV47 TRANSISTOR(NPN)

for preamplifier input applications



MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	30	V
Collector Emitter Voltage	V _{CEO}	30	V
Emitter Base Voltage	V _{EBO}	10	V
Collector Current	I _C	300	mA
Typical Thermal Resistance ¹⁾	R _{θJA}	556	°C/W
Total Power Dissipation	P _{tot}	225	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _s	-55 to +150	°C

1 Thermal resistance from junction to ambient at P.C.B. mounted

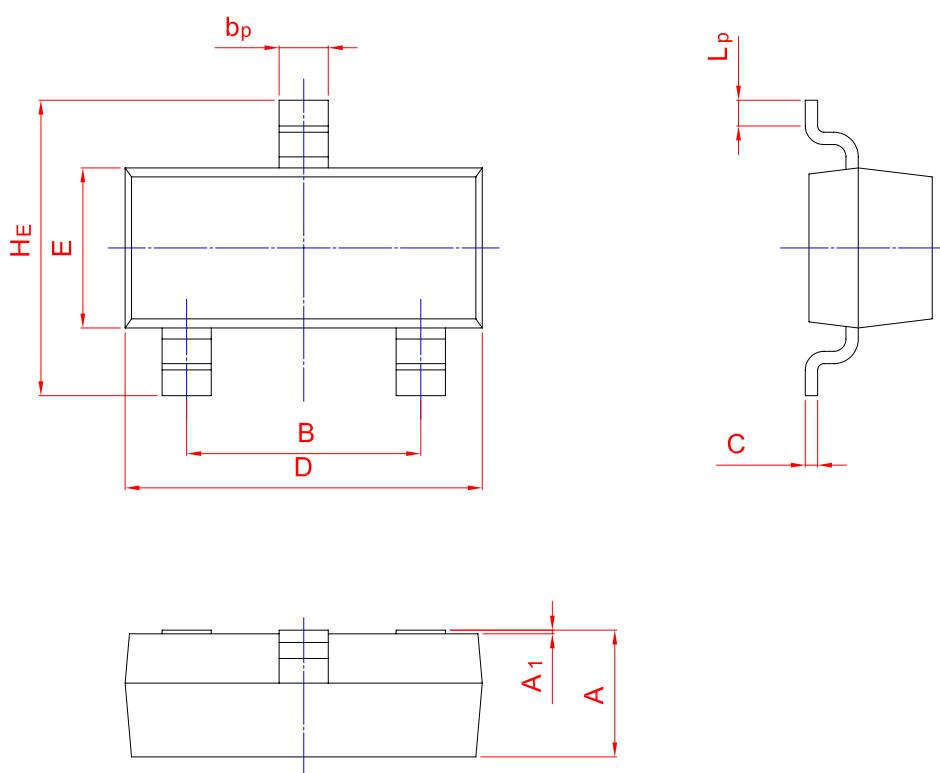
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V _{CE} = 5 V, I _C = 10 mA	h _{FE}	10000	-	-	-
at V _{CE} = 5 V, I _C = 100 mA	h _{FE}	20000	-	-	-
Collector Cutoff Current at V _{CB} = 30 V	I _{CBO}	-	-	100	nA
Collector Emitter Breakdown Voltage at I _C = 10 mA	V _{(BR)CEO}	30	-	-	V
Collector Emitter Saturation Voltage at I _C = 100 mA, I _B = 0.1 mA	V _{CE(sat)}	-	-	1.5	V
Base Emitter On-state Voltage at I _C = 100 mA, V _{CE} = 5 V	V _{BE(on)}	-	-	2.0	V
Transition Frequency at V _{CE} = 5 V, I _C = 50 mA, f = 100 MHz	f _T	125	-	-	MHz

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20